

# GAN-BASED RADIATION-EMITTING THIN-LAYERED SEMICONDUCTOR COMPONENT

Patent number: WO2004017430

Publication date: 2004-02-26

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Classification:

- International: H01L33/00

- european: H01L33/00B6B; H01L33/00C3B

Application number: WO2003DE02071 20030620

Priority number(s): DE20021034977 20020731

Also published as:

DE10234977 (A1)

CN1672270 (A)

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US6258618

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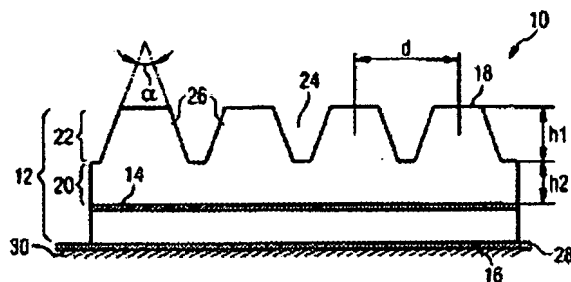
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## Abstract of WO2004017430

The invention relates to a radiation-emitting thin-layered semiconductor component comprising a GaN-based multilayer structure (12) that is provided with an active, radiation-generating layer (14), a first main area (16), and a second main area (18) that is located opposite the first main area and decouples the radiation generated in the active, radiation-generating layer. The first main area (16) of the multilayer structure (12) is coupled to a reflective layer or border area while the region (22) of the multilayer structure, which borders the second main area (18) thereof, is structured in a one-dimensional or two-dimensional manner and is provided with convex elevations (26).



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